

HiPerFET™

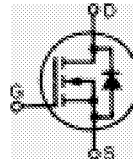
Power MOSFETs

IXFH/IXFT/IXFX14 N100
IXFH/IXFT/IXFX15 N100

N-Channel Enhancement Mode
High dv/dt, Low t_{rr} , HDMOS™ Family

V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	14 A	0.75 Ω
1000 V	15 A	0.70 Ω
$t_{rr} \leq 200$ ns		

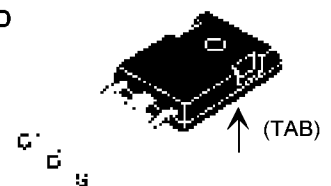
Preliminary data sheet



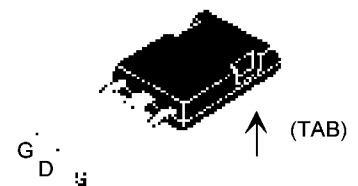
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	14N100 14 15N100 15	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	14N100 56 15N100 60	A
I_{AR}	$T_C = 25^\circ\text{C}$	14N100 14 15N100 15	A
E_{AR}	$T_C = 25^\circ\text{C}$	45	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	360	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 1$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20$ V $_{DC}$, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0$ V $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			250 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300$ μs , duty cycle $d \leq 2$ %	14N100 0.75 Ω 15N100 0.70 Ω		

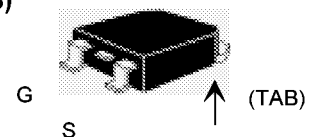
TO-247 AD
(IXFH)



PLUS 247™
(IXFX)



TO-268 (D3)
(IXFT)



Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole) or mounting clip or spring (PLUS 247™)
- High power surface mountable package
- High power density

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}, \text{ pulse test}$	6	10	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500 430 150	pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External),		27 30 120 30	ns ns ns ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		220 30 85	nC nC nC
R_{thJC} R_{thCK}	(TO-247 Case Style)		0.25	0.35 KW KW

Source-Drain Diode		Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	14N100 15N100		14 A 15 A
I_{SM}	Repetitive; pulse width limited by T _{JM}	14N100 15N100		56 A 60 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr} Q_{RM} I_{RM}	$I_F = I_S$ $-di/dt = 100\text{ A}/\mu\text{s},$ $V_R = 100\text{ V}$	T _J = 25°C T _J = 125°C T _J = 25°C T _J = 125°C T _J = 25°C T _J = 125°C	200 350 1 2 10 15	ns ns μC μC A A

TO-268 Outline		DIMENSIONS			
		INCHES		MILLIMETERS	
SYM		MIN	MAX	MIN	MAX
A		.193	.201	4.90	5.10
A1		.106	.114	2.70	2.90
A2		.001	.010	0.02	0.25
b		.045	.057	1.15	1.45
b2		.075	.083	1.90	2.10
C		.016	.026	0.40	0.65
C2		.057	.063	1.45	1.60
D		.543	.551	13.80	14.00
D1		.488	.500	12.40	12.70
E		.624	.632	15.85	16.05
E1		.524	.535	13.30	13.60
e		.215 BSC		5.45 BSC	
H		.736	.752	18.70	19.10
L		.094	.106	2.40	2.70
L1		.047	.055	1.20	1.40
L2		.039	.045	1.00	1.15
L3		.010 BSC		0.25 BSC	
L4		.150	.161	3.80	4.10

TO-247 AD (IXFH) Outline		DIMENSIONS			
		MILLIMETER		INCHES	
Dim.		Min.	Max.	Min.	Max.
A		4.7	5.3	.185	.209
A ₁		2.2	2.54	.087	.102
A ₂		2.2	2.6	.059	.098
b		1.0	1.4	.040	.055
b ₁		1.65	2.13	.065	.084
b ₂		2.87	3.12	.113	.123
C		.4	.8	.016	.031
D		20.80	21.46	.819	.845
E		15.75	16.26	.610	.640
e		5.20	5.72	0.205	0.225
L		19.81	20.32	.780	.800
L1			4.50		.177
ØP		3.55	3.65	.140	.144
Q		5.89	6.40	0.232	0.252
R		4.32	5.49	.170	.216
S		6.15 BSC		242 BSC	

PLUS 247™ Outline		DIMENSIONS			
		INCHES		MILLIMETERS	
SYM		MIN	MAX	MIN	MAX
A		.190	.205	4.83	5.21
A1		.090	.100	2.29	2.54
A2		.075	.085	1.91	2.16
B1		.045	.055	1.14	1.40
B2		.075	.084	1.91	2.13
D		.115	.123	2.92	3.12
D1		.064	.081	1.63	2.06
E		.619	.640	15.80	16.26
E1		.620	.635	15.75	16.13
e		.215 BSC		5.45 BSC	
L		.780	.800	19.81	20.32
L1		.150	.170	3.81	4.30
Q		.820	.844	20.83	21.44
R		.170	.190	4.32	4.83

Min Recommended Footprint		DIMENSIONS			
		INCHES		MILLIMETERS	
SYM		MIN	MAX	MIN	MAX
A		.653	1.659		
B				.197	5.00
C				.0531	1.349
D				.0864	2.195
E				.118	3.00
F				.0215	5.46

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

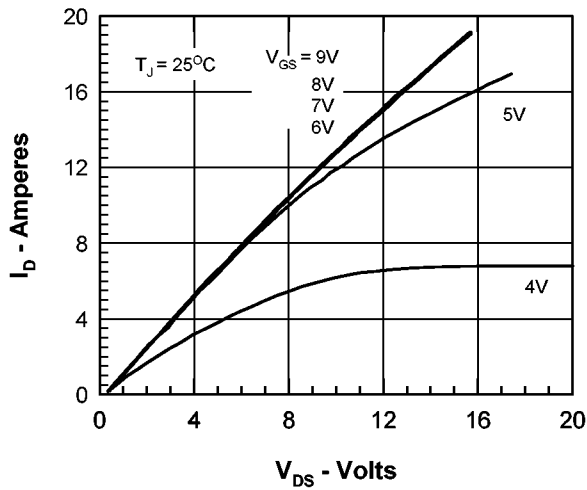


Fig.1 Output Characteristics

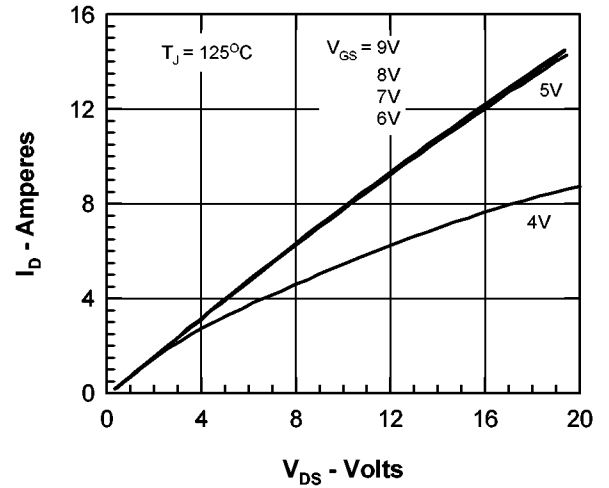


Fig.2 Output characteristics at elevated temperature

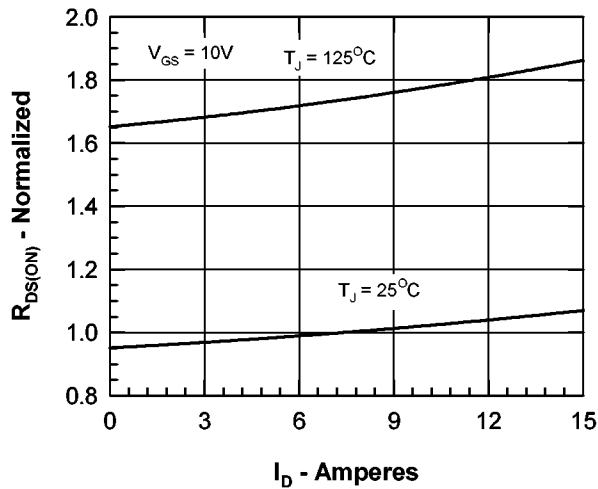


Fig.3 $R_{DS(on)}$ vs. Drain Current

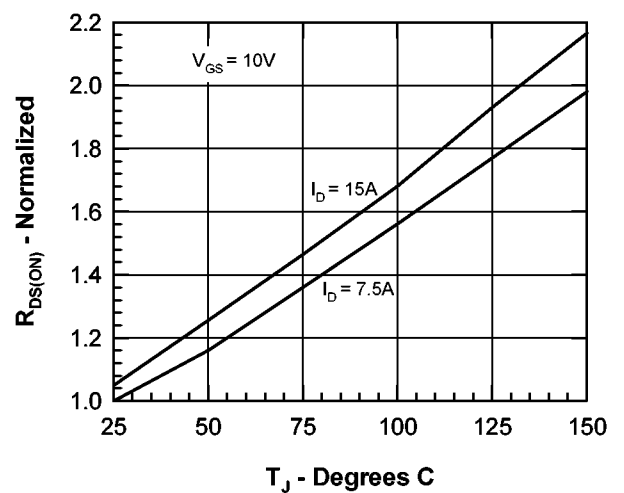


Fig.4 Temperature Dependence of Drain to Source Resistance

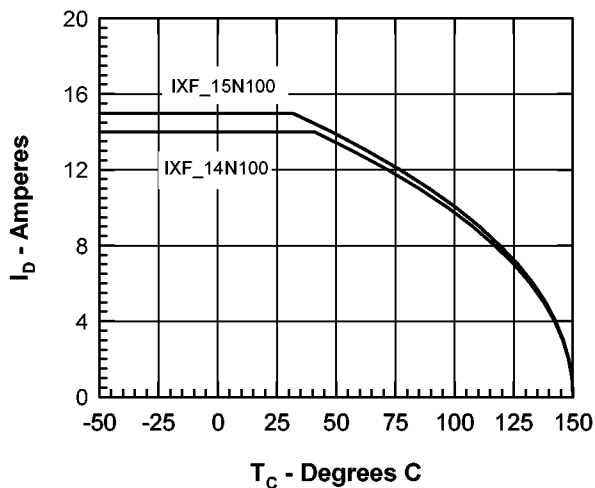


Fig.5 Drain Current vs. Case Temperature

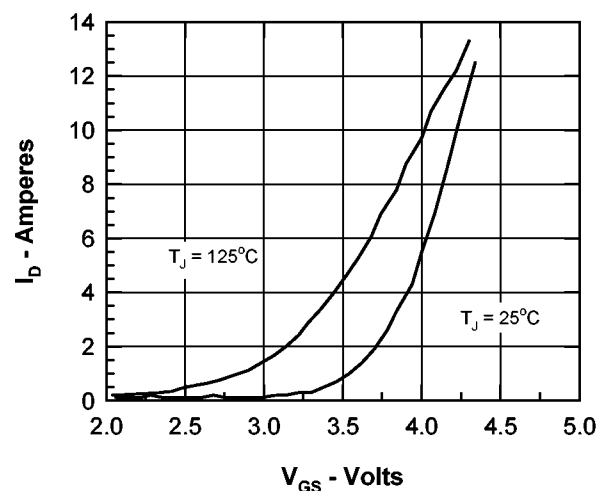


Fig.6 Input admittance

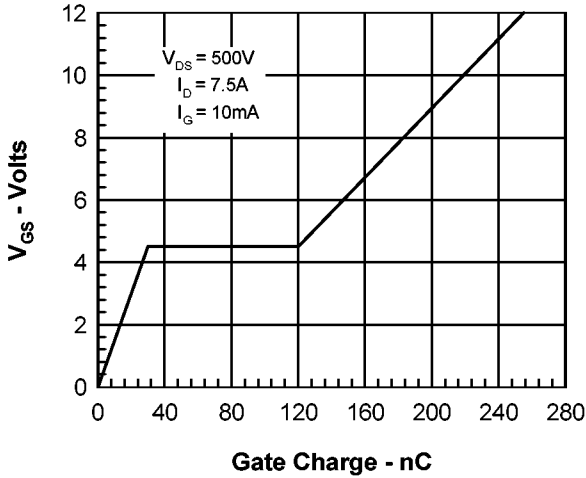


Fig.7 Gate Charge Characteristic Curve

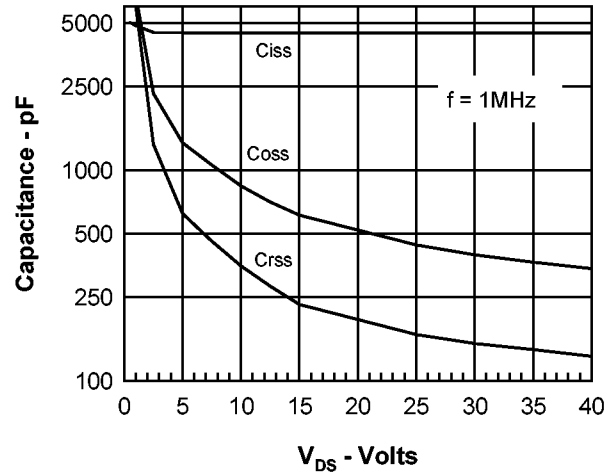


Fig.8 Capacitance Curves

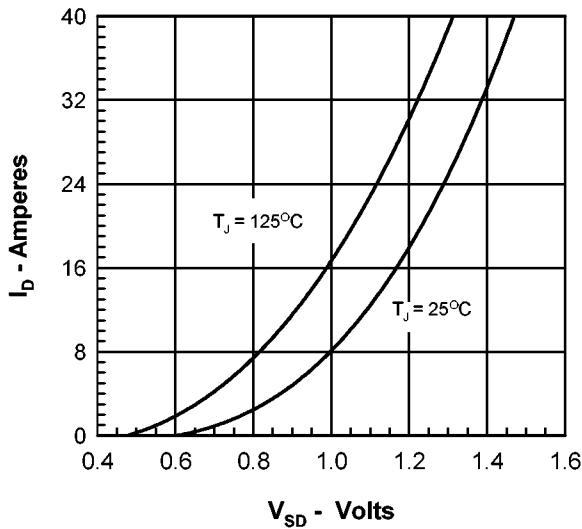


Fig.9 Source current vs Source drain voltage.

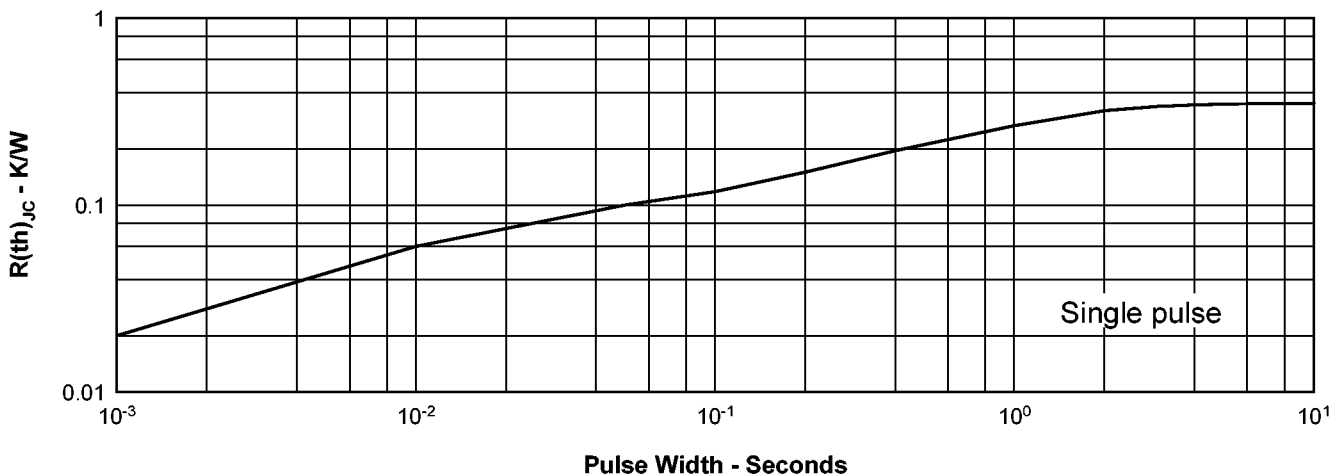


Fig.10 Transient Thermal Impedance